优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
30V	23mΩ @ V_{GS} = 10V	6.6A
	30mΩ @ V_{GS} = 4.5V	5.8A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Backlighting

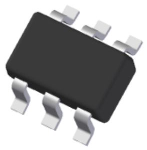
Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed

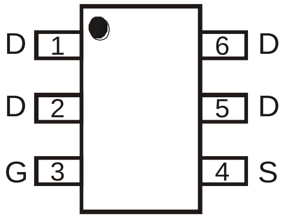
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, “Green” Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.013 grams (Approximate)

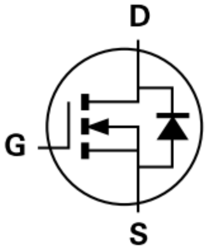
TSOT26



Top View



Top View
Pin Configuration



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	6.6 5.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	8.5 6.8	A
Maximum Body Diode Forward Current (Note 7)			I_S	3.0	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	35	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	100	°C/W
	t<10s		60	°C/W
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	1.5	W
	T_A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	$R_{\theta JA}$	83	°C/W
	t<10s		50	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	14.5	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	19	23	mΩ	V_{GS} = 10V, I_D = 6.5A
		—	22	30		V_{GS} = 4.5V, I_D = 6.0A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	643	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	65	—		
Reverse Transfer Capacitance	C_{rss}	—	49	—		
Gate Resistance	R_G	—	2.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	5.7	—	nC	V_{DS} = 15V, I_D = 4.0A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	12.5	—		
Gate-Source Charge	Q_{gs}	—	1.7	—		
Gate-Drain Charge	Q_{gd}	—	1.8	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.2	—	nS	V_{GS} = 10V, V_{DD} = 15V, R_G = 6.0Ω, I_D= 6.5A
Turn-On Rise Time	t_r	—	2.5	—		
Turn-Off Delay Time	$t_{D(off)}$	—	12.1	—		
Turn-Off Fall Time	t_f	—	3.0	—		
Body Diode Reverse Recovery Time	t_{rr}	—	6.5	—	nS	I_F = 6.5A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{rr}	—	1.7	—	nC	I_F = 6.5A, dI/dt = 100A/µs

Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

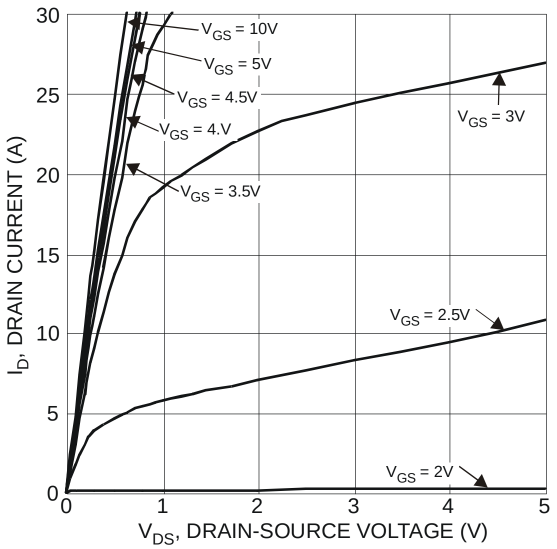


Figure 1 Typical Output Characteristics

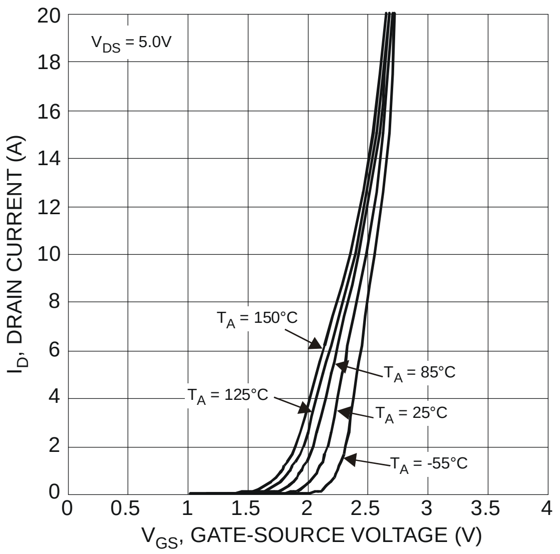


Figure 2 Typical Transfer Characteristics

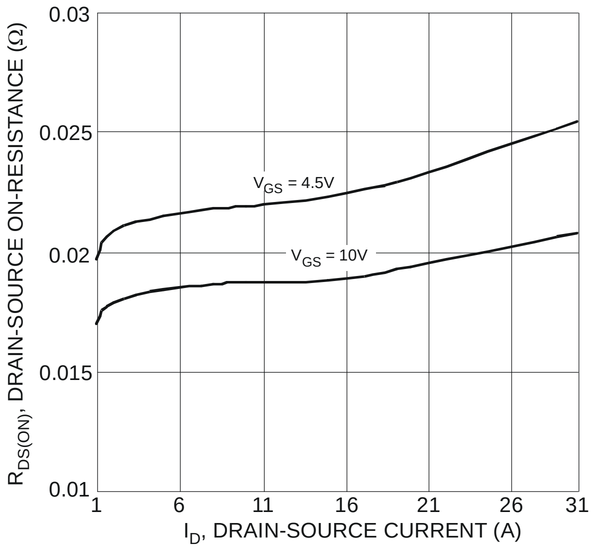


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

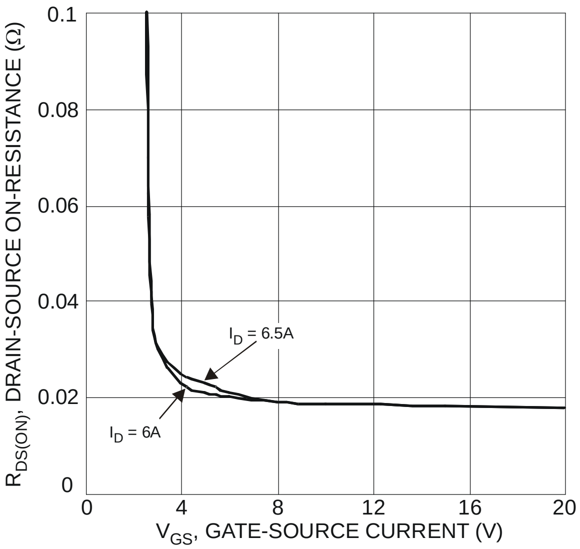


Figure 4 Typical Transfer Characteristics

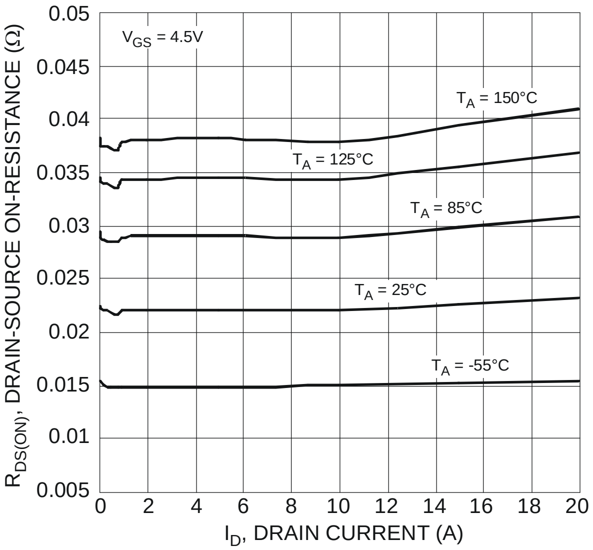


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

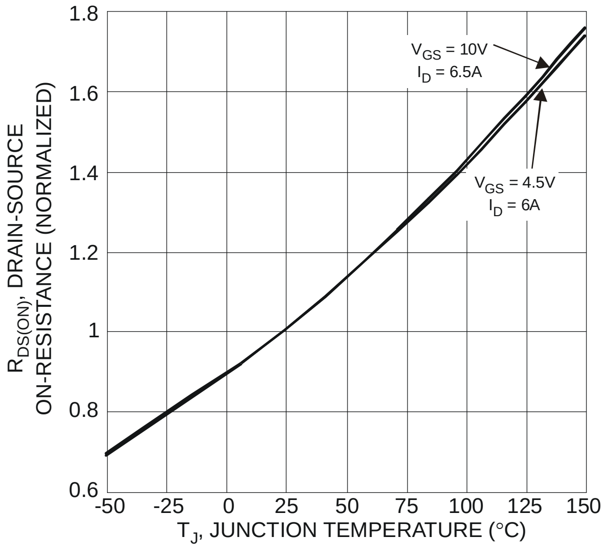


Figure 6 On-Resistance Variation with Temperature

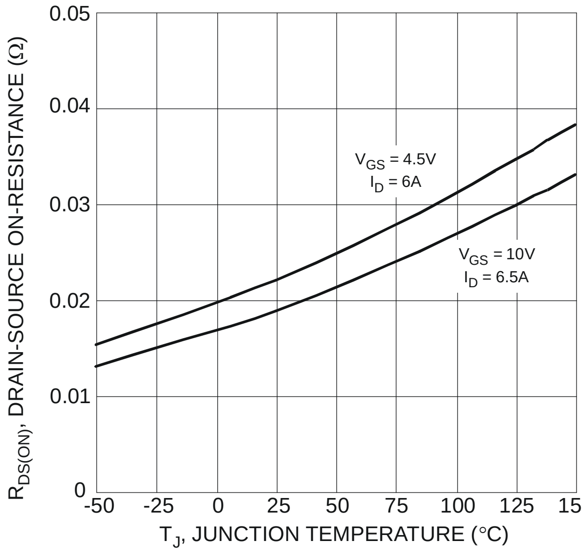


Figure 7 On-Resistance Variation with Temperature

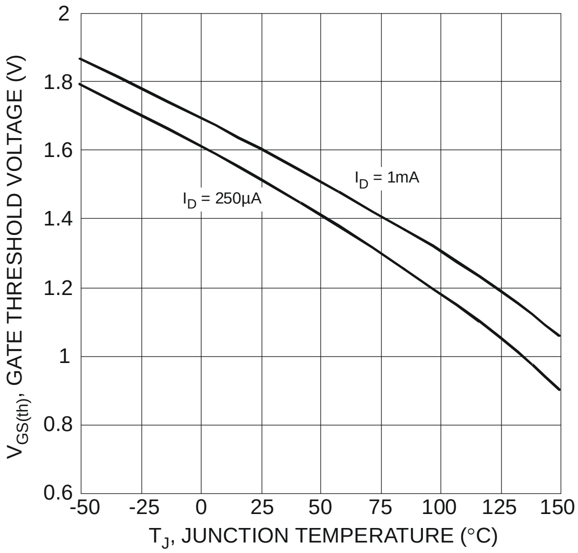


Figure 8 Gate Threshold Variation vs. Ambient Temperature

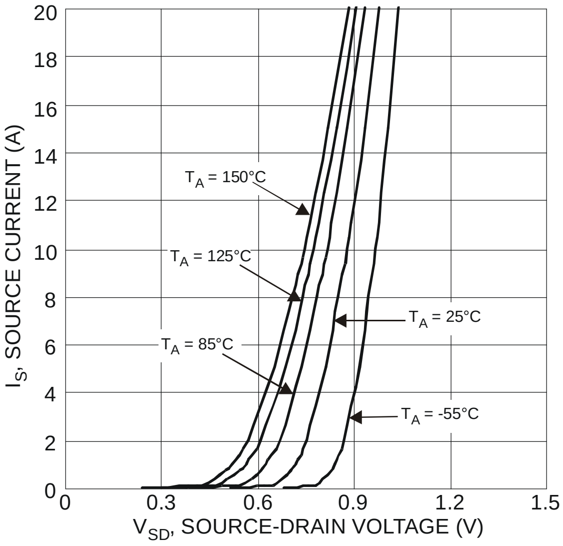


Figure 9 Diode Forward Voltage vs. Current

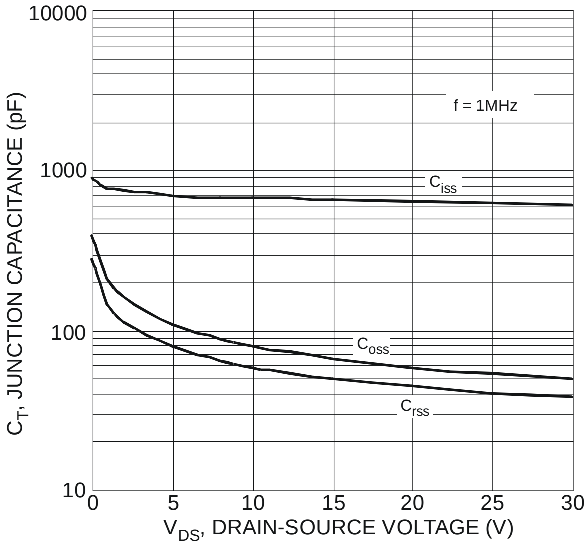


Figure 10 Typical Junction Capacitance

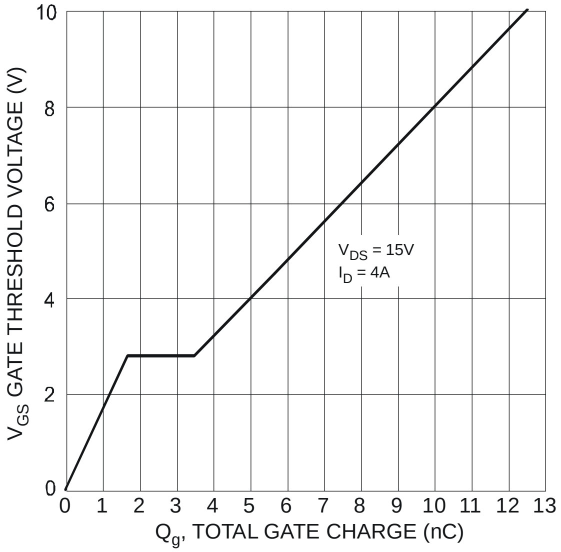


Figure 11 Gate Charge

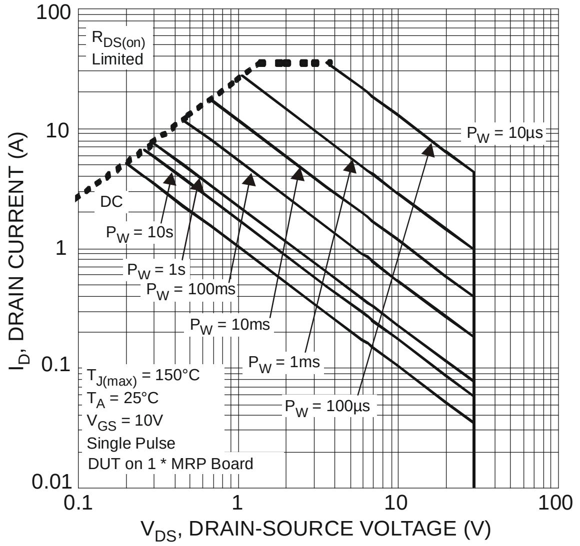


Figure 12 SOA, Safe Operation Area

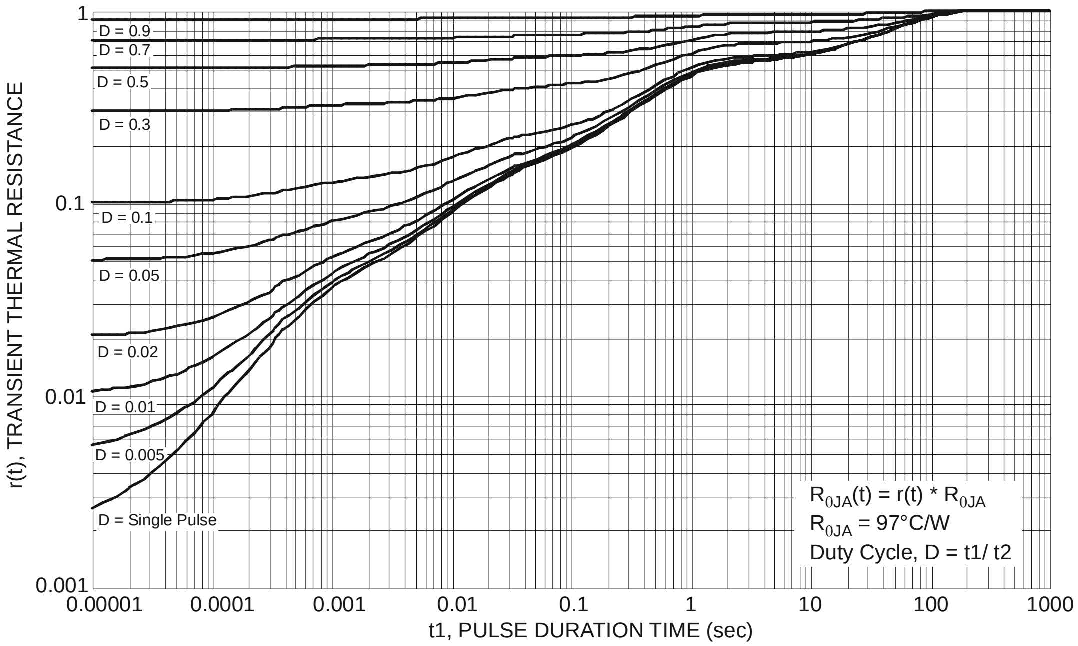
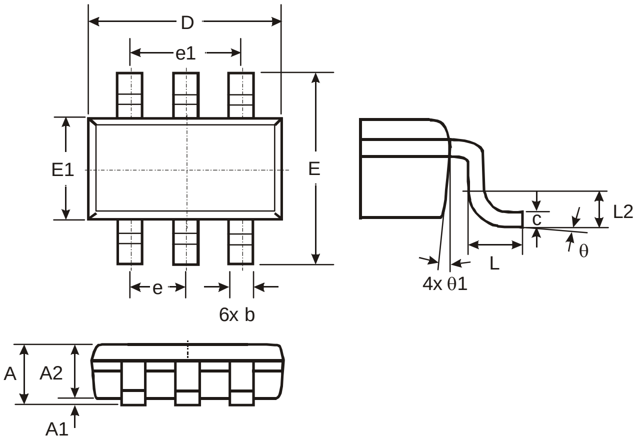


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

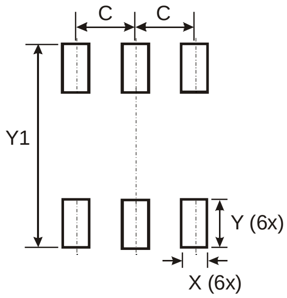
TSOT26



TSOT26			
Dim	**Min**	**Max**	**Typ**
A	—	1.00	—
A1	0.01	0.10	—
A2	0.84	0.90	—
D	—	—	2.90
E	—	—	2.80
E1	—	—	1.60
b	0.30	0.45	—
c	0.12	0.20	—
e	—	—	0.95
e1	—	—	1.90
L	0.30	0.50	—
L2	—	—	0.25
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199